

Euijun Cha

List of Publications by Year in descending order

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499
citing authors

#	ARTICLE	IF	CITATIONS
1	Comprehensive scaling study of NbO ₂ insulator-metal-transition selector for cross point array application. Applied Physics Letters, 2016, 108, .	3.3	84
2	Analog Synapse Device With 5-b MLC and Improved Data Retention for Neuromorphic System. IEEE Electron Device Letters, 2016, 37, 1067-1070.	3.9	42
3	Bidirectional threshold switching in engineered multilayer (Cu ₂ O/Ag:Cu ₂ O/Cu ₂ O) stack for cross-point selector application. Applied Physics Letters, 2015, 107, .	3.3	41
4	Engineering Oxygen Vacancy of Tunnel Barrier and Switching Layer for Both Selectivity and Reliability of Selector-Less ReRAM. IEEE Electron Device Letters, 2014, 35, 1022-1024.	3.9	24
5	Highly Reliable Resistive Switching Without an Initial Forming Operation by Defect Engineering. IEEE Electron Device Letters, 2013, 34, 1515-1517.	3.9	19
6	Internal resistor of multi-functional tunnel barrier for selectivity and switching uniformity in resistive random access memory. Nanoscale Research Letters, 2014, 9, 364.	5.7	19
7	NbO ₂ -Based Frequency Storable Coupled Oscillators for Associative Memory Application. IEEE Journal of the Electron Devices Society, 2018, 6, 250-253.	2.1	19
8	Selector-less ReRAM with an excellent non-linearity and reliability by the band-gap engineered multi-layer titanium oxide and triangular shaped AC pulse. , 2013, , .		18
9	Dependence of reactive metal layer on resistive switching in a bi-layer structure Ta/HfO _x filament type resistive random access memory. Applied Physics Letters, 2014, 104, 083507.	3.3	17
10	Thermally activated non-linearity of device in resistance-switching memory for cross-point array applications. Applied Physics Letters, 2013, 102, .	3.3	13
11	Multilayer-oxide-based bidirectional cell selector device for cross-point resistive memory applications. Applied Physics Letters, 2013, 103, .	3.3	13
12	Tunnel barrier engineering of titanium oxide for high non-linearity of selector-less resistive random access memory. Applied Physics Letters, 2014, 104, 052108.	3.3	11
13	Resistive-switching analogue memory device for neuromorphic application. , 2014, , .		3
14	Effects of High-Pressure Hydrogen Annealing on the Formation of Conducting Filaments in Filament-Type Resistive Random-Access Memory. Journal of Electronic Materials, 2014, 43, 3635-3639.	2.2	2
15	Effect of TiO ₂ -based tunnel barrier on non-linearity and switching reliability of resistive random access memory. , 2014, , .		1
16	A two-step set operation for highly uniform resistive switching ReRAM by controllable filament. , 2013, , .		0